IN THE CLAIMS

1-12. (Canceled).

13. (*Previously Presented*) A method for megasonic cleaning of semiconductor wafers comprising the steps of:

generating two or more parallel sets of megasonic waves in a cleaning fluid;

immersing semiconductors in the cleaning fluid;

moving the wafers in the cleaning fluid through said megasonic waves and transverse to the megasonic waves.

- 14. (*Original*) The method of claim 13 wherein the megasonic waves are generated across parallel regions of the fluid and the step of moving the wafers comprises reciprocating the wafers through said parallel regions.
- 15. (*Currently Amended*) A method for megasonic cleaning of semiconductor wafers comprising the steps of:

generating megasonic waves with a laminar flow in a cleaning fluid in a container;

5

PATENT 90065.161701(17732.6310.003) Reply to Final Office Action of 24 Nov. 2003

intercepting the generated waves inside the container and dispersing the waves in a divergent manner; and

exposing the semiconductor wafers to the dispersed megasonic waves within the cleaning fluid.

16-26. (Canceled).